

INCHANGE SEMICONDUCTOR

iscN-Channel MOSFET Transistor

TK17A80W, ITK17A80W

FEATURES

- Low drain-source on-resistance: $R_{DS}(ON) = 0.25\Omega$ (typ.)
- Enhancement mode: Vth = 3.0 to 4.0V (VDs = 10 V, ID=0.85mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

Switching Voltage Regulators

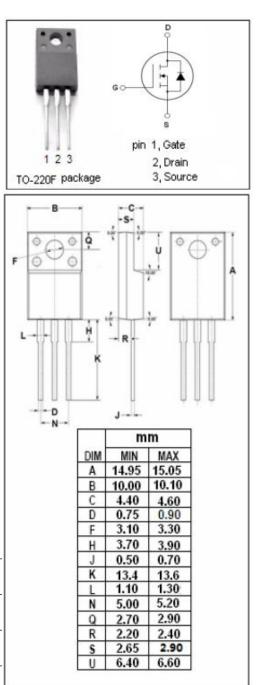
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT | | | |
|------------------|-------------------------------------|--------------------|------|--|--|--|
| V _{DSS} | Drain-Source Voltage | 800 | V | | | |
| V _{GS} | Gate-Source Voltage | ±20 | V | | | |
| ID | Drain Current-Continuous | 17 | А | | | |
| I _{DM} | Drain Current-Single Pulsed 68 | | А | | | |
| PD | Total Dissipation @Tc=25°C 45 | | W | | | |
| Tj | Max. Operating Junction Temperature | on Temperature 150 | | | | |
| T _{stg} | Storage Temperature | -55~150 | °C | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|-----------|------------------------------------------------|------|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 2.78 | °C/W |
| Rth(ch-a) | th(ch-a) Channel-to-ambient thermal resistance | | °C/W |

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iscN-Channel MOSFET Transistor TK1

TK17A80W, ITK17A80W

ELECTRICAL CHARACTERISTICS

 $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | МАХ | UNIT |
|----------------------|--------------------------------|-----------------------------------------------|-----|-----|-----|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 10mA | 800 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} = 10V; I _D =0.85mA | 3.0 | | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =8.5A | | 250 | 290 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V;V _{DS} = 0V | | | ±1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 800V; V _{GS} = 0V | | | 10 | μA |
| V _{SDF} | Diode forward voltage | I _{DR} =17A, V _{GS} = 0 V | | | 1.7 | v |

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